

OptiMOS™ Power-Transistor

Features

- Optimized for high performance SMPS, e.g. sync. rec.
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

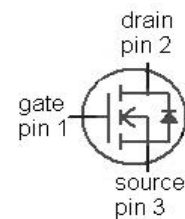
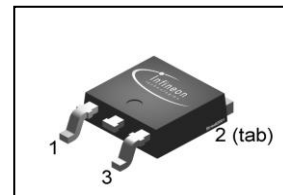


Type	Package	Marking
IPD053N06N	PG-TO252-3	053N06N

Product Summary

V_{DS}	60	V
$R_{DS(on),max}$	5.3	mΩ
I_D	45	A
Q_{OSS}	32	nC
$Q_G(0V..10V)$	27	nC

PG-TO252-3



Maximum ratings, at $T_J=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$	45	A
		$V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$	45	
		$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$, $R_{thJA}=50\text{K/W}$	18	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	180	
Avalanche energy, single pulse ³⁾	E_{AS}	$I_D=45\text{ A}$, $R_{GS}=25\text{ Ω}$	60	mJ
Gate source voltage	V_{GS}		±20	V

¹⁾ J-STD20 and JESD22

²⁾ See figure 3 for more detailed information

³⁾ See figure 13 for more detailed information

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	83	W
		$T_A=25\text{ °C}$, $R_{\text{thJA}}=50\text{ K/W}$	3.0	
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}	bottom	-	-	1.8	K/W
Device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ⁴⁾	-	-	40	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}$, $I_{\text{D}}=1\text{ mA}$	60	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{D}}=36\text{ }\mu\text{A}$	2.1	2.8	3.3	
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}}=60\text{ V}$, $V_{\text{GS}}=0\text{ V}$, $T_j=25\text{ °C}$	-	0.5	1	μA
		$V_{\text{DS}}=60\text{ V}$, $V_{\text{GS}}=0\text{ V}$, $T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{\text{GS}}=20\text{ V}$, $V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{ V}$, $I_{\text{D}}=45\text{ A}$	-	4.5	5.3	m Ω
		$V_{\text{GS}}=6\text{ V}$, $I_{\text{D}}=12\text{ A}$	-	6.0	8.0	
Gate resistance	R_{G}		-	1.5	2.3	Ω
Transconductance	g_{fs}	$ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}$, $I_{\text{D}}=45\text{ A}$	38	75	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=30\text{ V},$ $f=1\text{ MHz}$	-	2000	2500	pF
Output capacitance	C_{oss}		-	490	613	
Reverse transfer capacitance	C_{rss}		-	22	44	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30\text{ V}, V_{GS}=10\text{ V},$ $I_D=45\text{ A},$ $R_{G,ext,ext}=3\ \Omega$	-	12	-	ns
Rise time	t_r		-	12	-	
Turn-off delay time	$t_{d(off)}$		-	20	-	
Fall time	t_f		-	7	-	

Gate Charge Characteristics⁵⁾

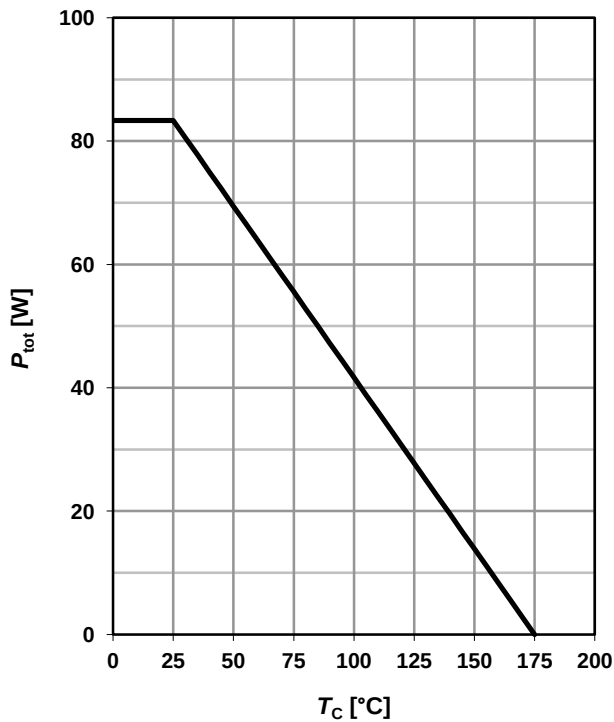
Gate to source charge	Q_{gs}	$V_{DD}=30\text{ V}, I_D=45\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	9	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	5	-	
Gate to drain charge	Q_{gd}		-	5	7	
Switching charge	Q_{sw}		-	9	-	
Gate charge total	Q_g		-	27	32	
Gate plateau voltage	$V_{plateau}$		-	4.8	-	V
Gate charge total, sync. FET	$Q_{g(sync)}$	$V_{DS}=0.1\text{ V},$ $V_{GS}=0\text{ to }10\text{ V}$	-	24	-	nC
Output charge	Q_{oss}	$V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$	-	32	-	

Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ °C}$	-	-	45	A
Diode pulse current	$I_{S,pulse}$		-	-	180	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=45\text{ A},$ $T_J=25\text{ °C}$	-	1.0	1.2	V
Reverse recovery time	t_{rr}	$V_R=30\text{ V}, I_F=45\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	32	51	ns
Reverse recovery charge	Q_{rr}		-	28	-	nC

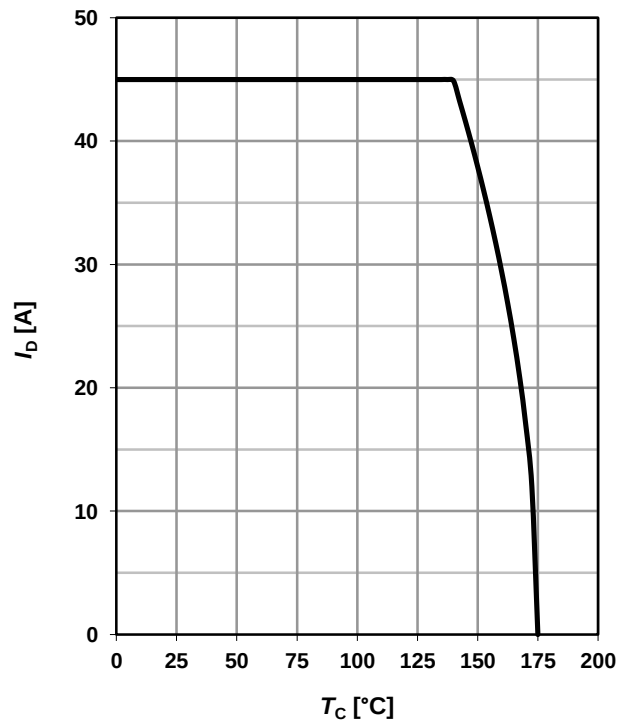
1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



2 Drain current

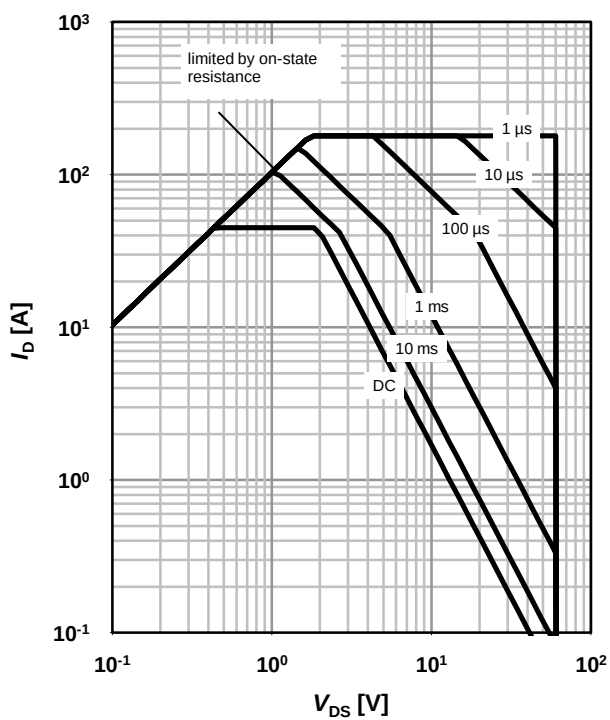
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

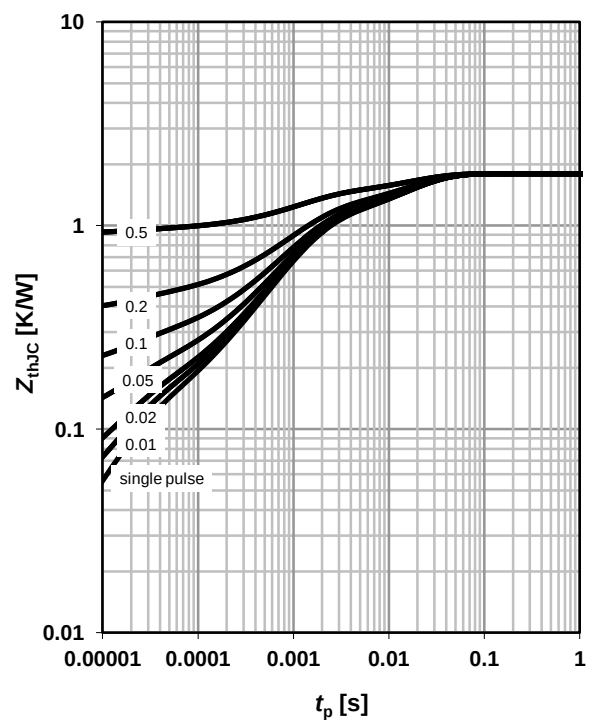
parameter: t_p



4 Max. transient thermal impedance

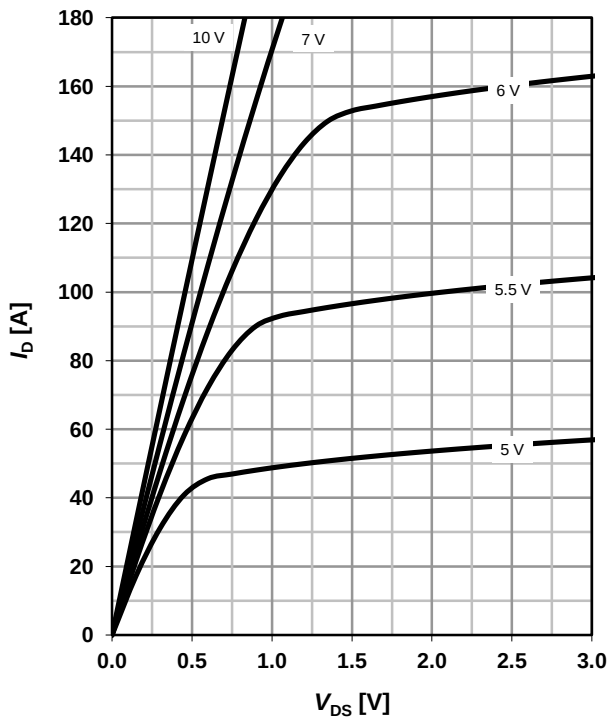
$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p / T$



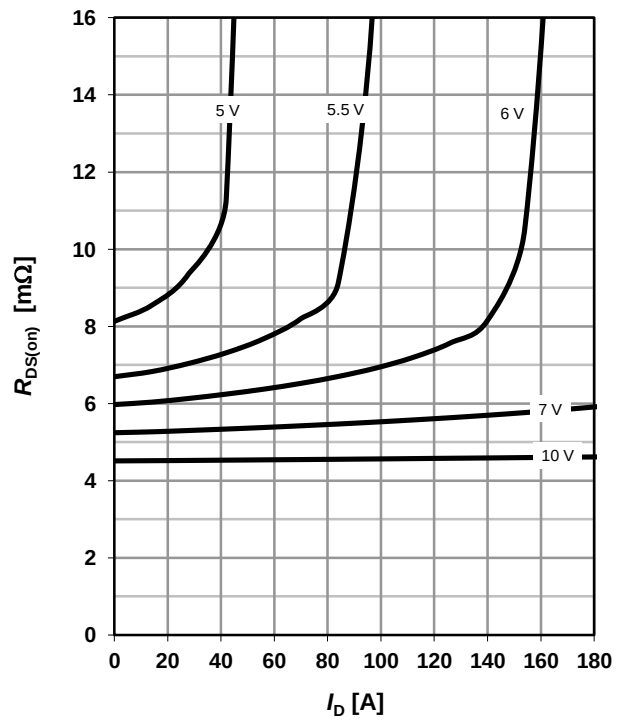
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: V_{GS}


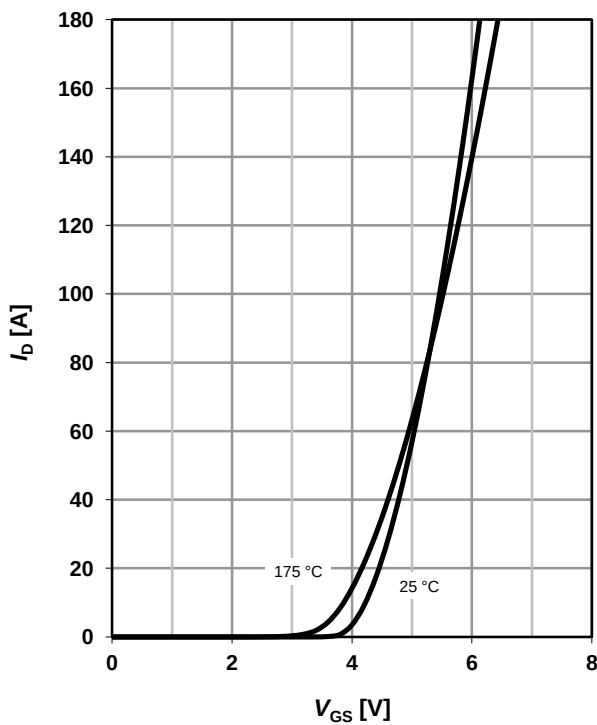
6 Typ. drain-source on resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

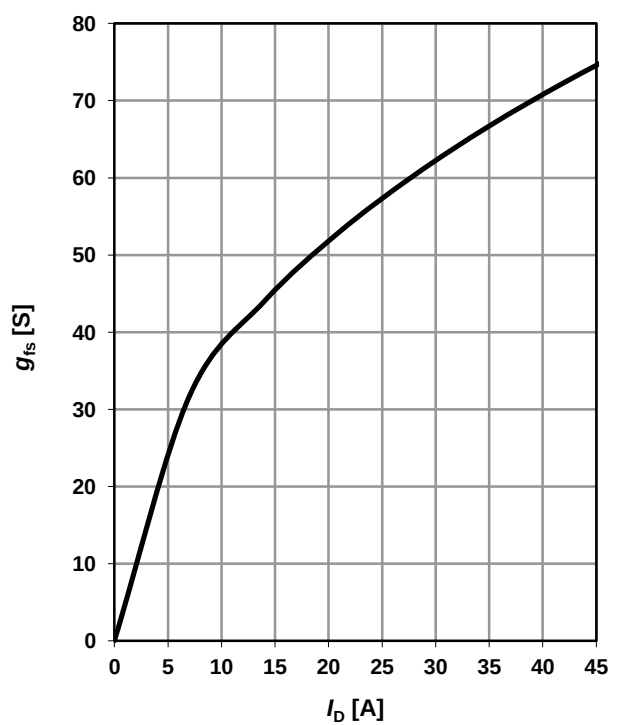
parameter: V_{GS}


7 Typ. transfer characteristics

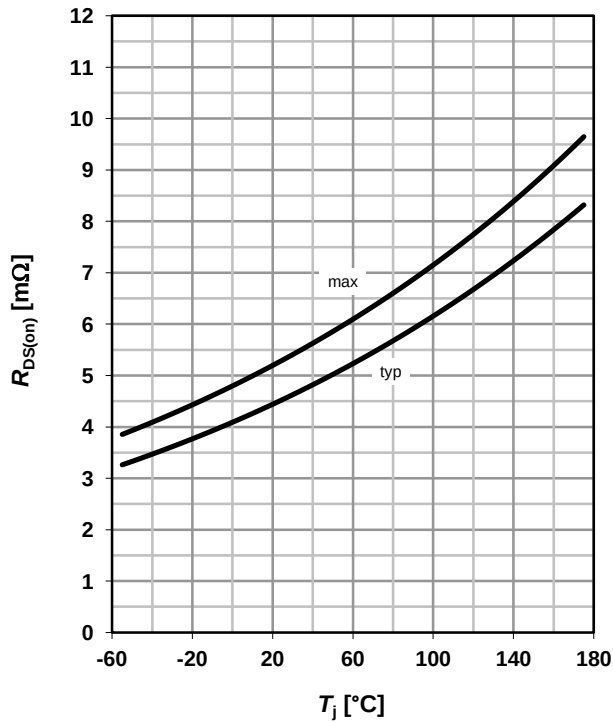
 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j


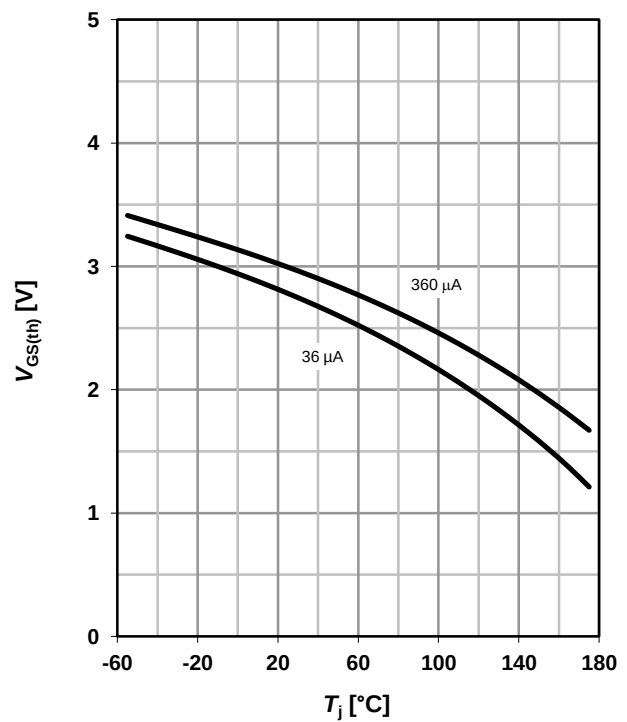
8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$


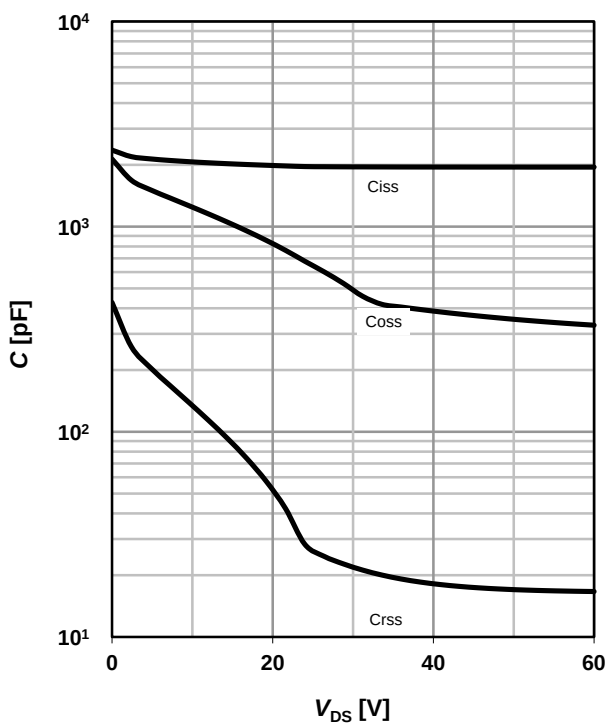
9 Drain-source on-state resistance

 $R_{DS(on)} = f(T_j); I_D = 45 \text{ A}; V_{GS} = 10 \text{ V}$


10 Typ. gate threshold voltage

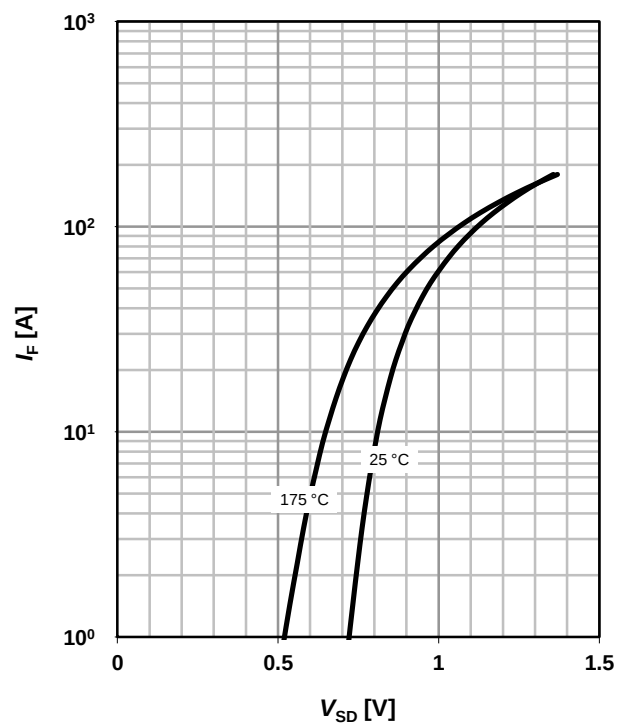
 $V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$


11 Typ. capacitances

 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$


12 Forward characteristics of reverse diode

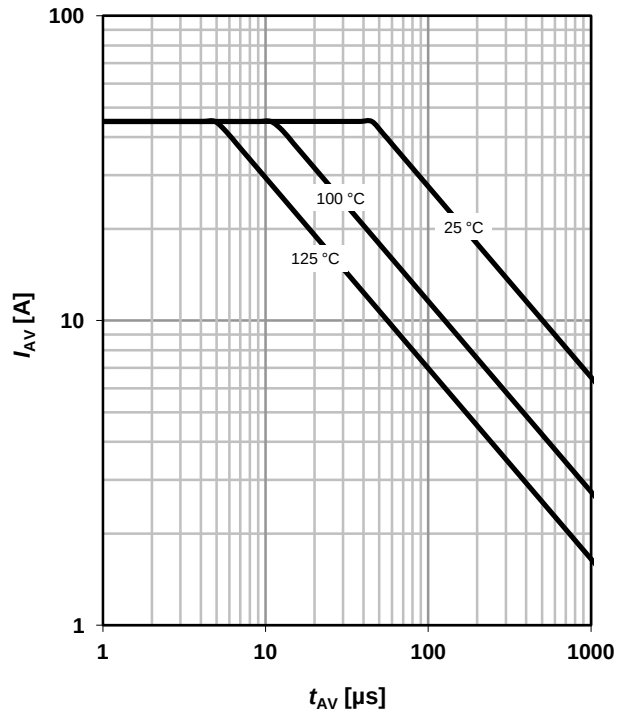
 $I_F = f(V_{SD})$

parameter: T_j


13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

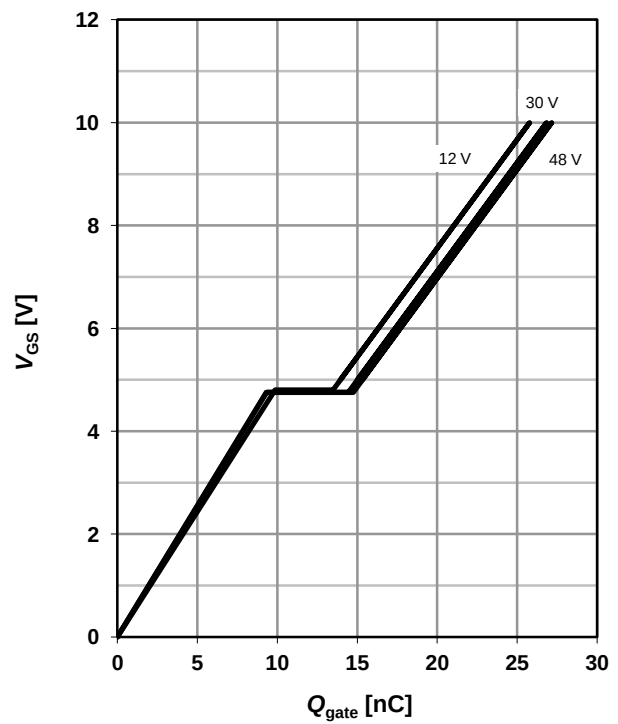
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

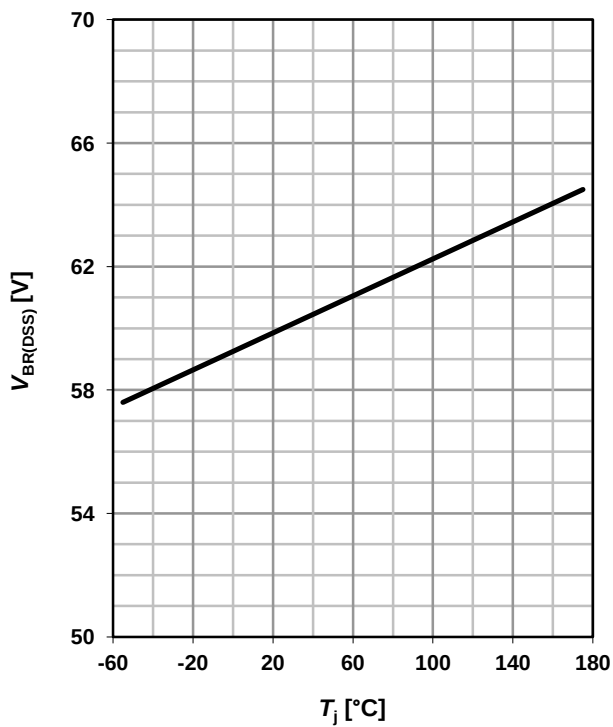
$$V_{GS}=f(Q_{\text{gate}}); I_D=45\ \text{A pulsed}$$

parameter: V_{DD}

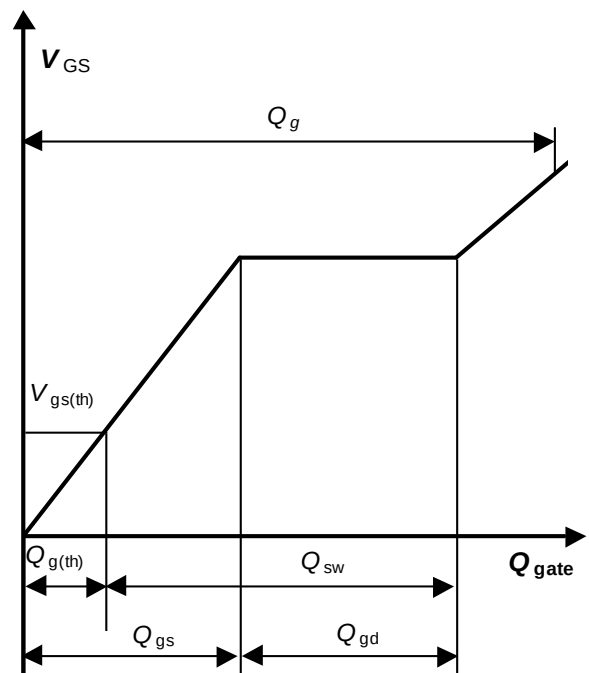


15 Drain-source breakdown voltage

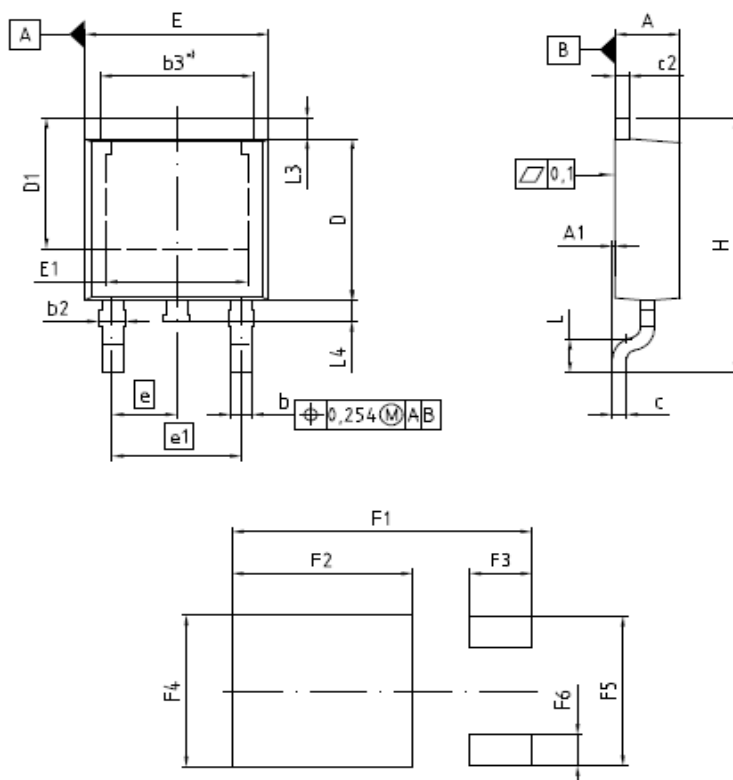
$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



16 Gate charge waveforms

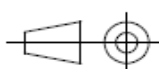


TO252-3 (DPAK)



*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.60		0.417	
F2	6.40		0.252	
F3	2.20		0.087	
F4	5.80		0.228	
F5	5.76		0.227	
F6	1.20		0.047	

DOCUMENT NO. Z8B00003328
SCALE 0 2.0 4mm
EUROPEAN PROJECTION 
ISSUE DATE 16-02-2011
REVISION 04

Published by
Infineon Technologies AG
81726 Munich, Germany
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